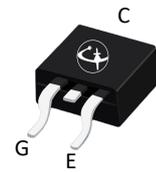
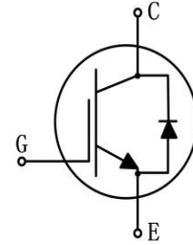


MAIN CHARACTERISTICS

I_C @TC=100°C	30A
V_{CE}	650V
VCE(sat)-typ	1.7V



TO-263C

FEATURES

- Positive temperature coefficient
- Fast Switching
- Low VCE(sat)
- Reliable and Rugged
- Halogen Free and Green Devices Available (RoHS Compliant)

APPLICATIONS

- UPS
- Motor drives
- Boost
- Portable power station

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LGT30N65T	TO-263C	LGT30N65T	Tape

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	650	V
Gate-emitter voltage	V_{GES}	± 30	V
Continuous collector current (TC=25°C)	I_C	60	A
Continuous collector current (TC=100°C)		30	A
Pulsed collector current, tp limited by Tvjmax	I_{CM}	90	A
Diode continuous forward current (TC=25°C)	I_F	60	A
Diode continuous forward current (TC=100°C)		30	A
Diode maximum current, tp limited by Tvjmax	I_{FM}	90	A
Short Circuit with Stand Time $V_{GE}=15V, V_{CC} \leq 400V$, Allowed Number of Short Circuits < 1000, Times Between Short Circuits $\geq 1.0s$, $T_J \leq 175^\circ C$	tsc	8	μS
Power dissipation (TC=25°C)	P_{tot}	170	W
Operating junction temperature range	T_{Jmax}, T_{Stg}	-55 to +175	°C
Maximum Temperature for Soldering	T_L	260	°C

Thermal characteristics

Parameter	Symbol	Values	Unit
Thermal resistance, junction to case for IGBT	$R_{th(j-c)}$	0.88	K/ W
Thermal resistance, junction to case for Diode	$R_{th(j-c)}$	1.12	K/ W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	62.5	K/ W

Note1: Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical characteristics of IGBT at $T_{vj}=25^\circ C$ unless otherwise specified

Static characteristics

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{GE}=0V, I_C=250\mu A$	BV_{CES}	650	-	-	V
Collector-emitter leakage current	$V_{CE}=650V, V_{GE}=0V$	I_{CES}	-	-	10	μA
Gate leakage current, forward	$V_{GE}=\pm 20V, V_{CE}=0V$	I_{GES}	-	-	± 200	nA
Gate-emitter threshold voltage	$V_{GE}=V_{CE}, I_C=1mA$	$V_{GE(th)}$	4.3	5.3	6.3	V
Collector-emitter saturation voltage	$V_{GE}=15V, I_C=30A, T_{vj}=25^\circ C$	$V_{CE(sat)}$	-	1.7	2.05	V
	$V_{GE}=15V, I_C=30A, T_{vj}=125^\circ C$		-	1.9	-	V
	$V_{GE}=15V, I_C=30A, T_{vj}=175^\circ C$		-	2.05	-	V
Diode forward voltage	$I_F=30A, T_{vj}=25^\circ C$	V_F	-	1.65	2.05	V
	$I_F=30A, T_{vj}=125^\circ C$		-	1.5	-	V
	$I_F=30A, T_{vj}=175^\circ C$		-	1.43	-	V

Electrical characteristics of IGBT at $T_{vj}=25^{\circ}\text{C}$ unless otherwise specified

Dynamic characteristics

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Input capacitance	$V_{CE}=25\text{V}$	C_{ies}	-	1840	-	pF
Output capacitance	$V_{GE}=0\text{V}$	C_{oes}	-	111	-	pF
Reverse transfer capacitance	$f=1\text{MHz}$	C_{res}	-	49	-	pF
Total gate charge	$V_{CC}=520\text{V}$ $V_{GE}=15\text{V}$ $I_C=30\text{A}$	Q_g	-	98	-	nC
Gate-Emitter Charge		Q_{ge}	-	18	-	nC
Gate-Collector Charge		Q_{gc}	-	47	-	nC

Switching characteristics

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Turn-on delay time	$V_{CC}=400\text{V}$ $V_{GE}=15\text{V}$ $I_C=30\text{A}$ $R_G=5\Omega$ Inductive load	$t_{d(on)}$	-	16	-	ns
Rise time		t_r	-	46	-	ns
Turn-off delay time		$t_{d(off)}$	-	72	-	ns
Fall time		t_f	-	80	-	ns
Turn-on energy		E_{on}	-	0.52	-	mJ
Turn-off energy		E_{off}	-	0.77	-	mJ
Total switching energy		E_{ts}	-	1.29	-	mJ
Turn-on delay time	$V_{CC}=400\text{V}$ $V_{GE}=15\text{V}$ $I_C=30\text{A}$ $R_G=5\Omega$ Inductive load $T_{vj}=175^{\circ}\text{C}$	$t_{d(on)}$	-	18	-	ns
Rise time		t_r	-	54	-	ns
Turn-off delay time		$t_{d(off)}$	-	90	-	ns
Fall time		t_f	-	75	-	ns
Turn-on energy		E_{on}	-	0.97	-	mJ
Turn-off energy		E_{off}	-	1.36	-	mJ
Total switching energy		E_{ts}	-	2.33	-	mJ

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Diode reverse recovery time	$V_R=400\text{V}$	t_{rr}	-	48	-	ns
Diode peak reverse recovery current	$I_F=30\text{A}$	I_{rrm}	-	5.1	-	A
Diode reverse recovery charge	$diF/dt=-200\text{A}/\mu\text{s}$	Q_{rr}	-	80	-	nC
Diode reverse recovery time	$V_R=400\text{V}$	t_{rr}	-	39	-	ns
Diode peak reverse recovery current	$I_F=30\text{A}$	I_{rrm}	-	8.5	-	A
Diode reverse recovery charge	$diF/dt=-200\text{A}/\mu\text{s}$ $T_{vj}=175^{\circ}\text{C}$	Q_{rr}	-	127	-	nC

RATINGS AND CHARACTERISTIC CURVES

Figure 1: Power Dissipation

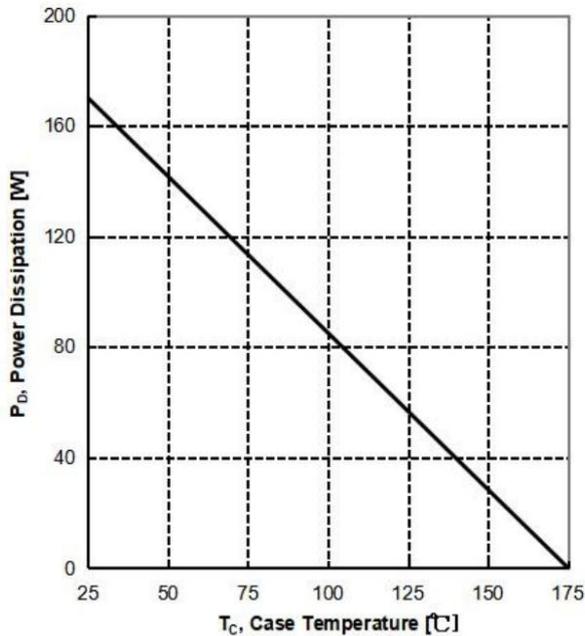


Figure 2: Collector Current vs. Case Temperature

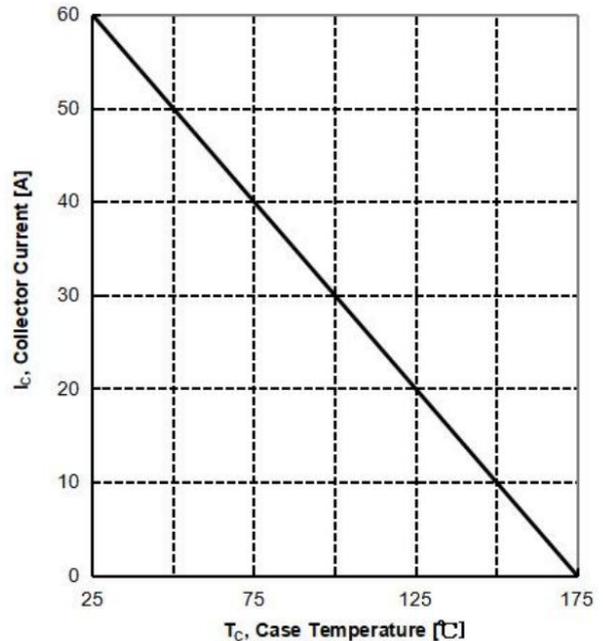


Figure 3: Safe Operation Area

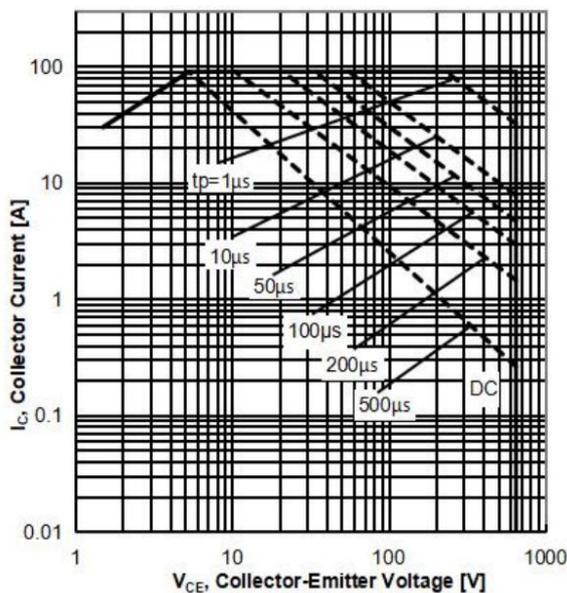
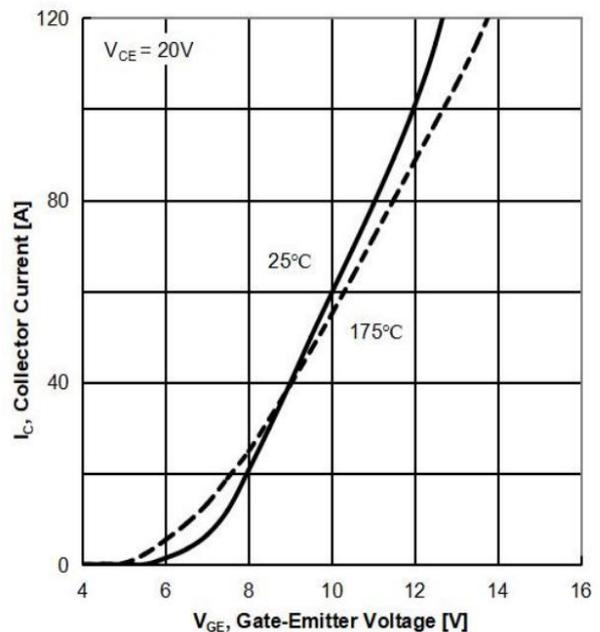


Figure 4: Typical Transfer Characteristics



RATINGS AND CHARACTERISTIC CURVES

Figure 5: Typical Output Characteristics

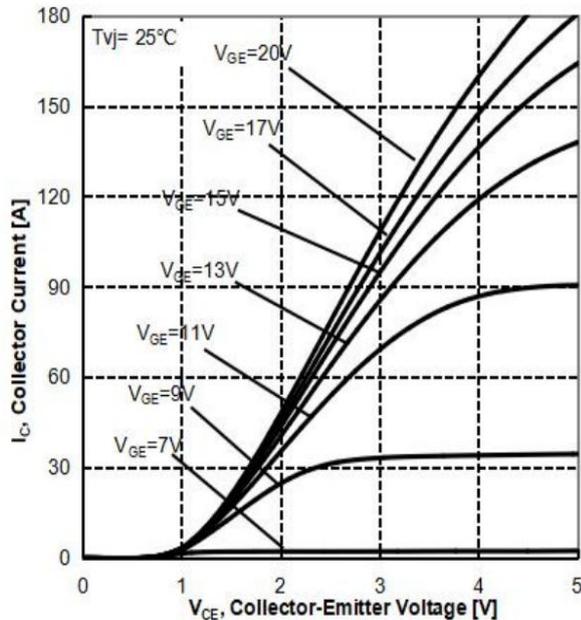


Figure 6: Typical Output Characteristics

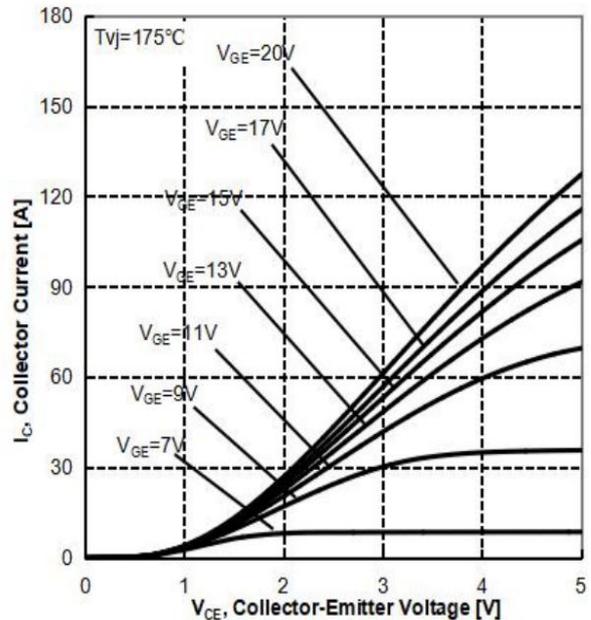


Figure 7: Typical Collector-Emitter Saturation Voltage vs. Junction Temperature

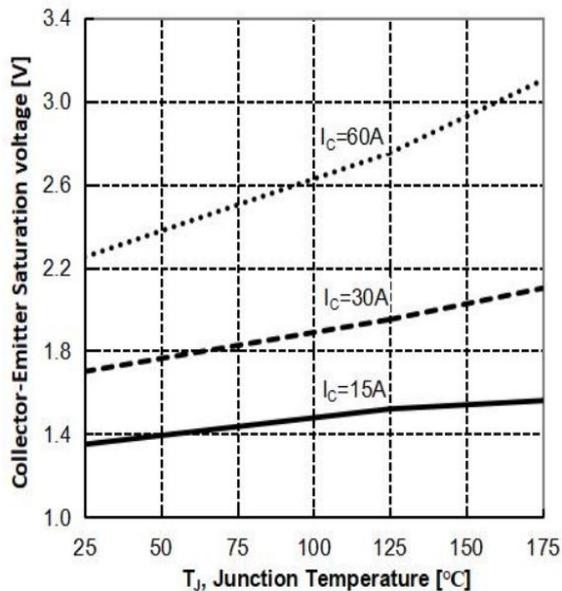
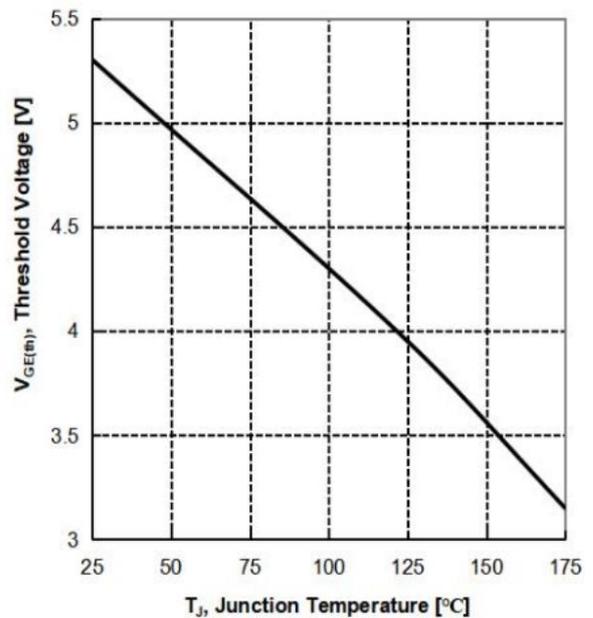


Figure 8: Typical Gate-Emitter Threshold Voltage vs. Junction Temperature



RATINGS AND CHARACTERISTIC CURVES

Figure 9: Typical Switching Times vs. Gate Resistor ($T_J=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $I_C=30\text{A}$)

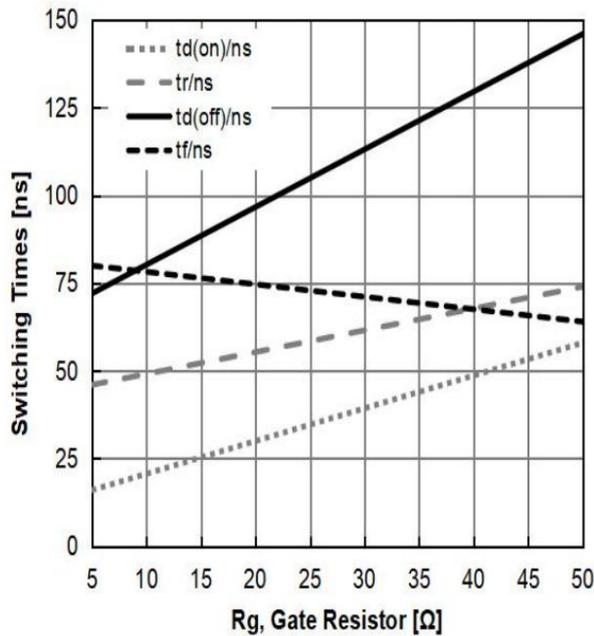


Figure 10: Typical Switching Energy vs. Gate Resistor ($T_J=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $I_C=30\text{A}$)

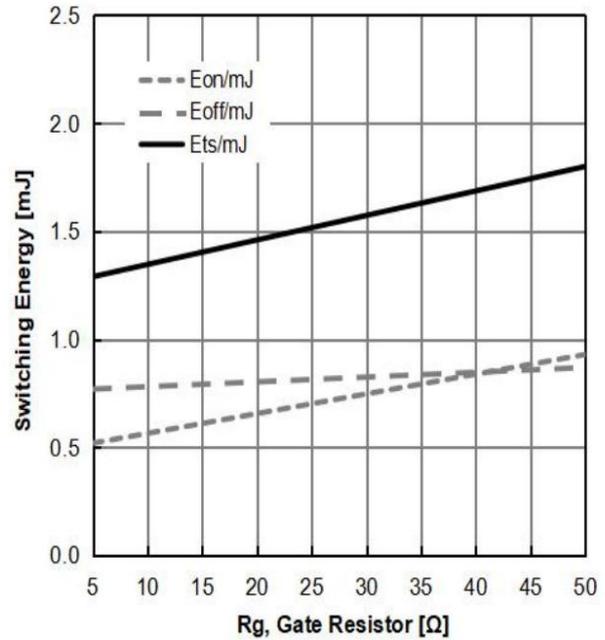


Figure 11: Typical Switching Times vs. Junction Temperature ($V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $I_C=30\text{A}$, $R_g=5\Omega$)

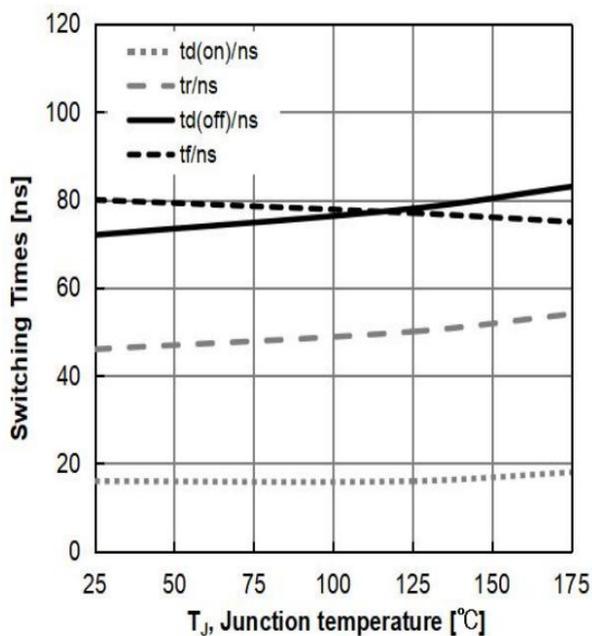
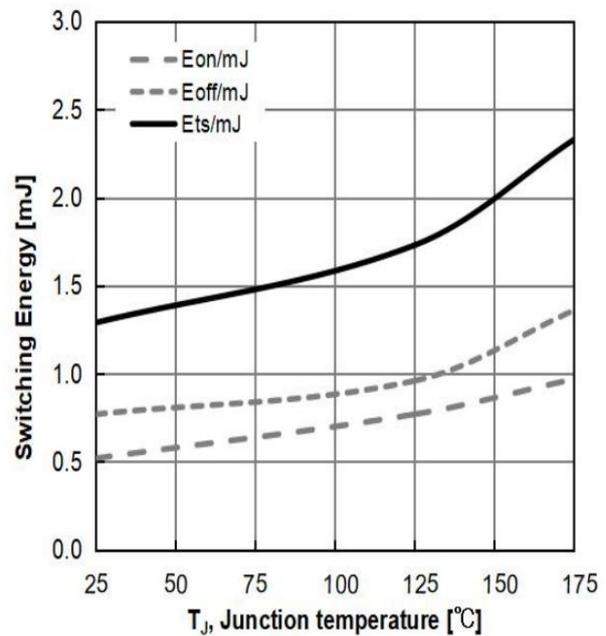


Figure 12: Typical Switching Energy vs. Junction Temperature ($V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $I_C=30\text{A}$, $R_g=5\Omega$)



RATINGS AND CHARACTERISTIC CURVES

Figure 13: Typical Switching Times vs. Collector Current ($T_J=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $R_g=5\Omega$)

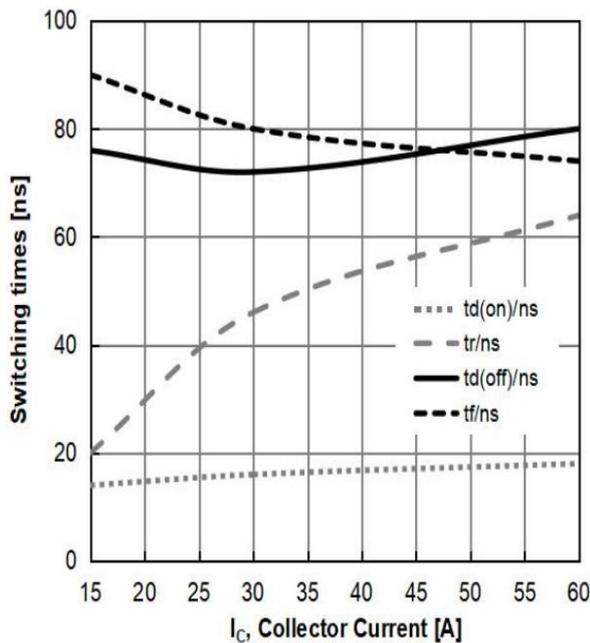


Figure 14: Typical Switching Energy vs. Collector Current ($T_J=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $R_g=5\Omega$)

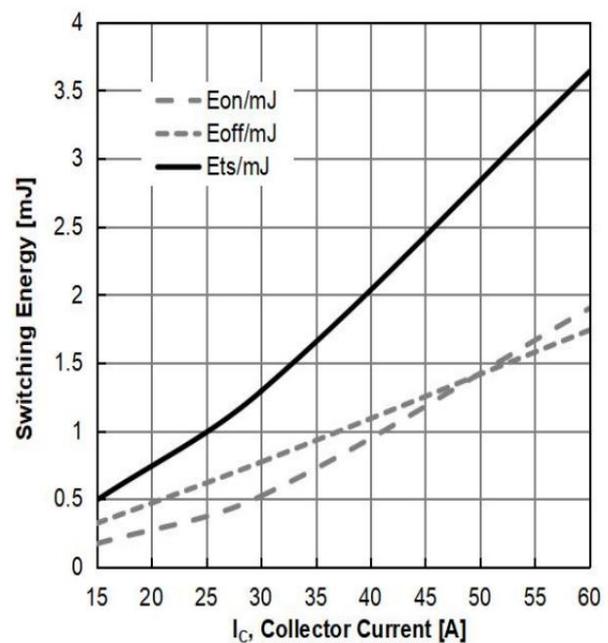


Figure 15: Typical Switching Times vs. VCE ($T_J=25^\circ\text{C}$, $V_{GE}=15\text{V}$, $I_C=30\text{A}$, $R_g=5\Omega$)

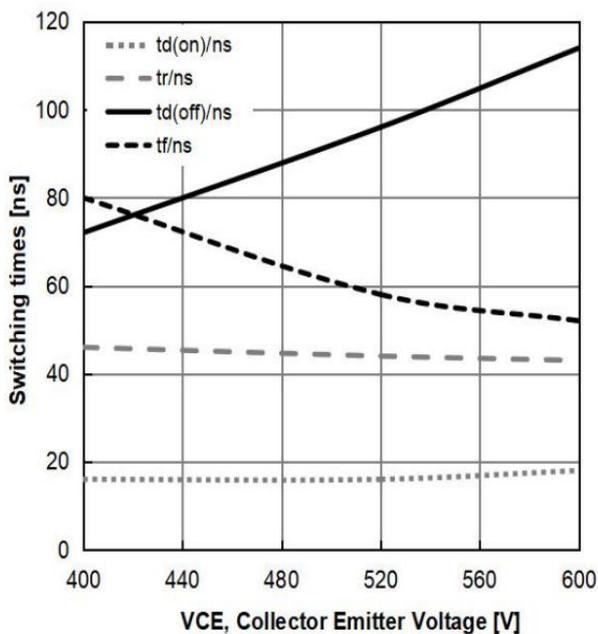
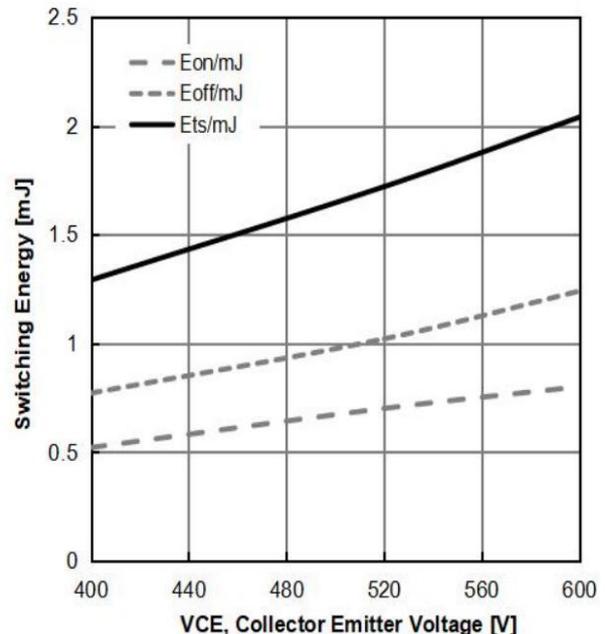


Figure 16: Typical Switching Energy vs. VCE ($T_J=25^\circ\text{C}$, $V_{GE}=15\text{V}$, $I_C=30\text{A}$, $R_g=5\Omega$)



RATINGS AND CHARACTERISTIC CURVES

Figure 17: Typical Capacitance vs. Collector-Emitter Voltage

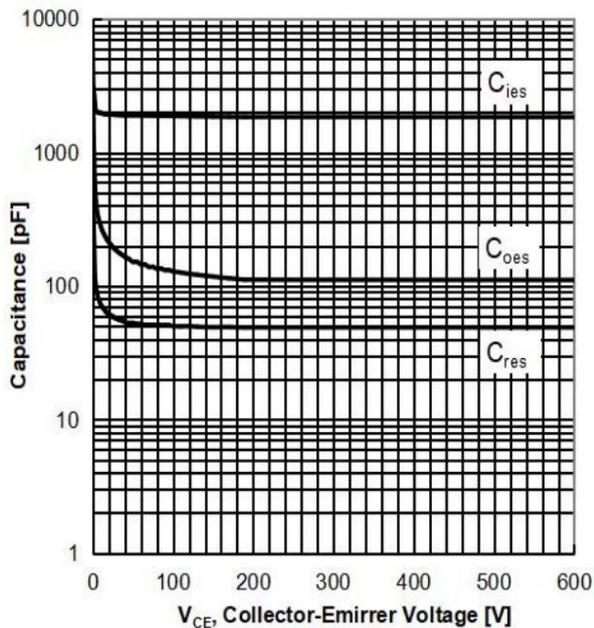


Figure 18: Typical Gate Charge

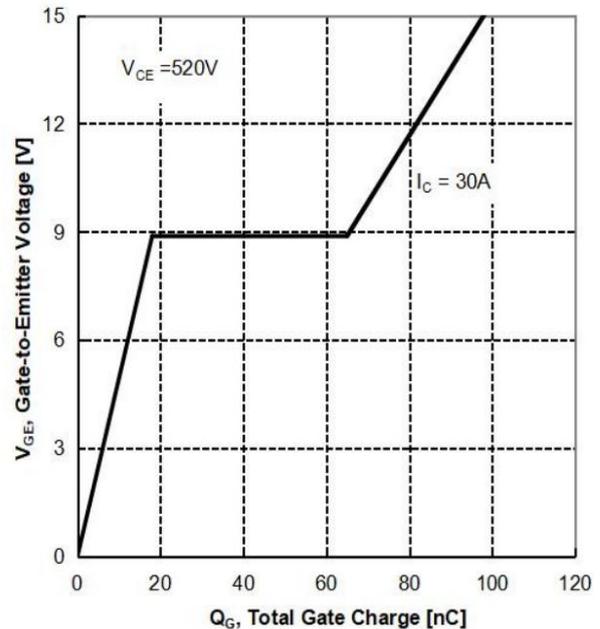


Figure 19: IGBT Transient Thermal Impedance vs. Pulse Width

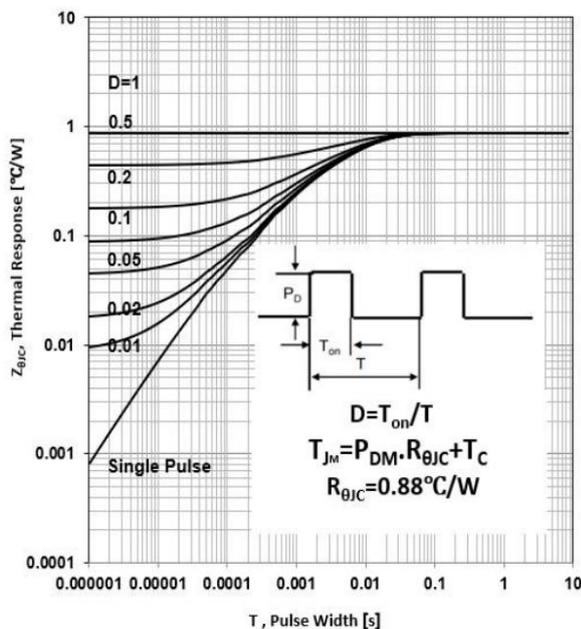


Figure 20: Diode Transient Thermal Impedance vs. Pulse Width

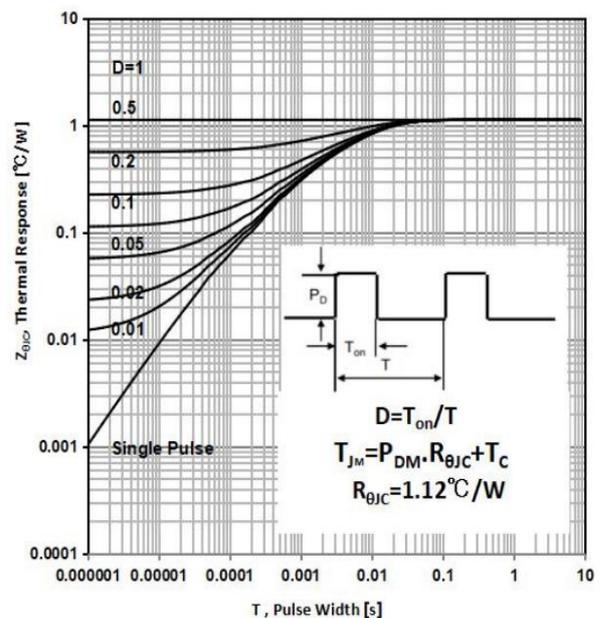
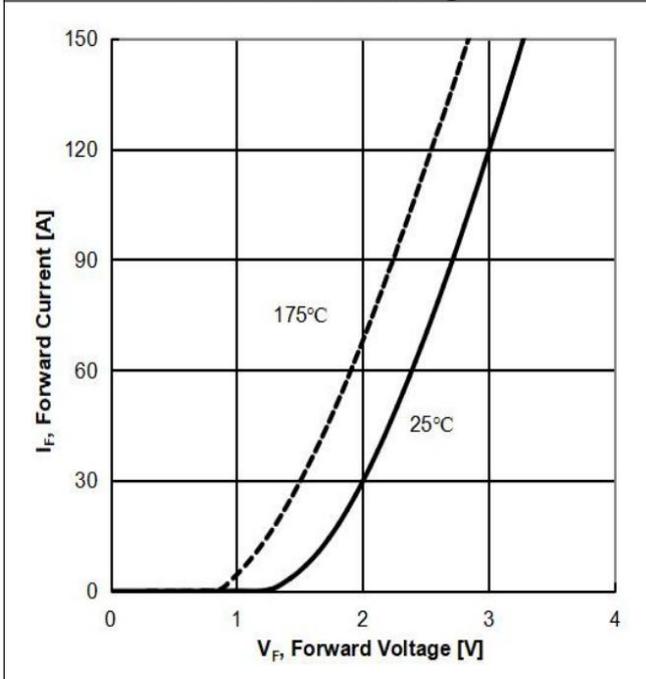
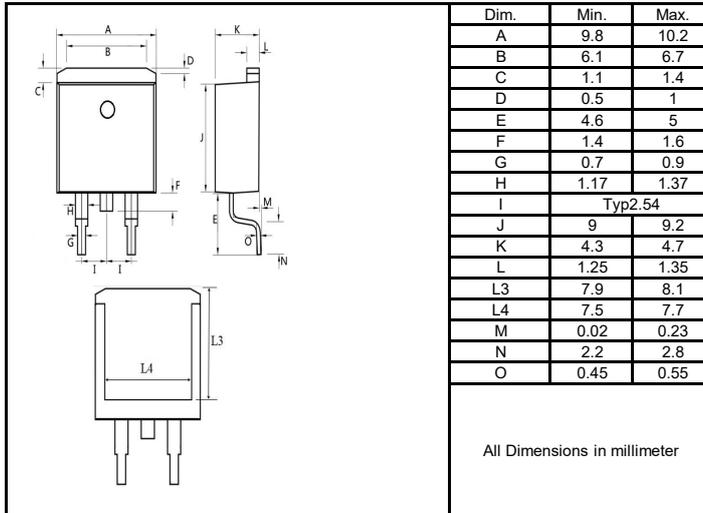


Figure 21: Typical Diode Forward Current vs. Forward Voltage

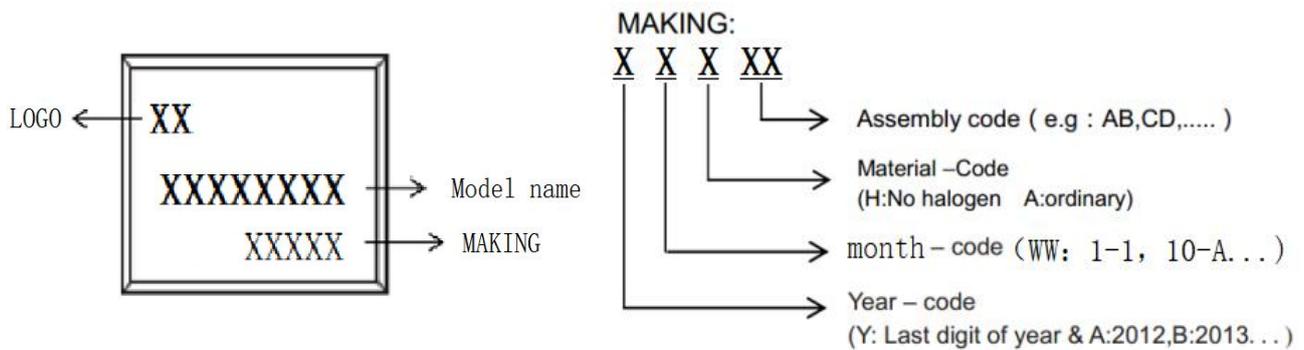


Package Outline Dimensions millimeters

T0-263C



Marking on the body



packing instruction

PKG	Minimal Package	Mini Box	Box
TO-263C			
	800pcs/disk	1600pcs/disk	8000pcs/box



LGT30N65T

N-Channel Enhancement Mode Power IGBT

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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Revision History

Rev	Changes	Date
1.0	First version	2025-7-18